

Title (en)

UNIVERSAL SEMICONDUCTOR WAFER FOR HIGH-VOLTAGE SEMICONDUCTOR COMPONENTS

Title (de)

UNIVERSAL-HALBLEITERSCHEIBE FÜR HOCHVOLT-HALBLEITERBAUELEMENTE

Title (fr)

PLAQUETTE DE SEMICONDUCTEUR UNIVERSELLE POUR COMPOSANTS A SEMICONDUCTEUR HAUTE TENSION

Publication

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Application

EP 99915461 A 19990208

Priority

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Abstract (en)

[origin: DE19816448C1] The invention relates to a universal semiconductor wafer for high-voltage semiconductor components in which at least one layer (5, 6, 7) of a first conduction type is provided on a semiconductor substrate (4) of a first conduction type. A plurality of floating semiconductor regions (8) of the other conduction type are embedded in the boundary surfaces between the semiconductor substrate (4) and the at least one layer. These semiconductor regions are measured such that the measurement of a semiconductor region (8) is smaller compared to the layer thickness of the semiconductor layer (5, 6, 7) and is essentially equal to or less than the distance between the floating semiconductor regions (8) in a boundary surface.

IPC 1-7

H01L 29/06

IPC 8 full level

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